

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising;
an analog buffer comprising at least ~~one thin film transistor~~ one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors; and
a channel forming ~~region~~ regions of the first and second thin film ~~transistor~~ transistors, each of the channel forming ~~region~~ regions comprising a polycrystalline semiconductor layer,
wherein a gate length of the first and second thin film ~~transistor~~ transistors is 7 μm or longer.

2. (Original) A semiconductor device according to claim 1, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

3. (Currently Amended) A semiconductor device comprising;
an analog buffer comprising at least ~~one thin film transistor~~ one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors; and
a channel forming ~~region~~ regions of the first and second thin film ~~transistor~~ transistors, each of the channel forming ~~region~~ regions comprising a polycrystalline semiconductor layer,
wherein a gate width of the first and second thin film ~~transistor~~ transistors is 50 μm or longer.

4. (Original) A semiconductor device according to claim 3, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

5. (Currently Amended) A semiconductor device comprising;
an analog buffer comprising at least ~~one thin film transistor~~ one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors; and
a channel ~~forming region~~ regions of the first and second thin film ~~transistor~~ transistors, each of the channel ~~forming region~~ regions comprising a polycrystalline semiconductor layer,
wherein a gate length of the first and second thin film ~~transistor~~ transistors is 7 μm or longer and a gate width of the first and second thin film ~~transistor~~ transistors is 50 μm or longer.

6. (Original) A semiconductor device according to claim 5, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

7-14. (Cancelled).

15. (Original) A semiconductor device comprising:
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors,
wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,
wherein a gate length of each of the first and second thin film transistors is 7 μm or longer;
wherein the first and second thin film transistors are connected in parallel with each other; and
wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

16. (Original) A semiconductor device according to claim 15, wherein a gate width of the respective thin film transistors is 50 μm or longer.

17. (Original) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type.

18. (Original) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type and a gate width of the respective thin film transistors is 50 μm or longer.

19. (Original) A semiconductor device according to claim 15, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

20. (Original) A semiconductor device comprising:
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,
wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,
wherein a gate width of each of the first and second thin film transistors is 50 μm or longer;
wherein the first and second thin film transistors are connected in parallel with each other; and
wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

21. (Original) A semiconductor device according to claim 20, wherein the respective thin film transistors is multi-gate type.

22. (Original) A semiconductor device according to claim 20, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

23. (Original) A semiconductor device comprising:
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,
wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,
wherein each of the first and second thin film transistors is multi-gate type
wherein the first and second thin film transistors are connected in parallel with each other; and
wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

24. (Original) A semiconductor device according to claim 23, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

25. (Original) A semiconductor device comprising:
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,
wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,
wherein a gate length of each of the first and second thin film transistors is 7 μm or

longer; wherein the first and second thin film transistors are connected in parallel with each other and located in a cross arrangement; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

26. (Original) A semiconductor device according to claim 25, wherein the device is selected from the group consisting of a liquid crystal display, an EL display a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

27. (Original) A semiconductor device comprising:
an analog buffer comprising a source follower comprising a plurality of thin film transistors; and
a channel region of the respective thin film transistors, comprising a polycrystalline semiconductor layer;
wherein the respective thin film transistors is a multi-gate type;
wherein a gate length of the respective thin film transistors is 7 μm or longer and a gate width of the respective thin film transistors is 50 μm or longer;
wherein the plurality of thin film transistors are connected in parallel with each other, and
wherein gate electrodes of the plurality of thin film transistors are connected to a same potential.

28. (Original) A semiconductor device according to claim 27, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.